				Sheet I of I	
	Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-586002	Application No. 10/802,331	
	Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Lawrence D. Wong		
			Filing Date March 16, 2004	Group Art Unit 2826	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
/S.R.W./	AA	7,030,468	04/18/2006	Gates et al.			
	AB						
	AC						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner	Desig.	Document	Publication	Country or			Trans	Translation
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
	AD							
	AE							
	AF							

Other Documents (include Author, Title, Date, and Place of Publication)					
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/S.R.W./	AG	Baklanov, M.R., et al., "Comparative study of Porous SOG Films with Different Non-Destructive Intermentation", Proceedings of the IEEE 2001 International Interconnect Technology Conference, pp. 189-191, June 2001.			
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Examiner Signature /Scott Wilson/	Date Considered 09/12/2008
EXAMINER: Initials citation considered. Draw line through citation if no next communication to applicant.	t in conformance and not considered. Include copy of this form with